

TO-92 Plastic-Encapsulate Transistors

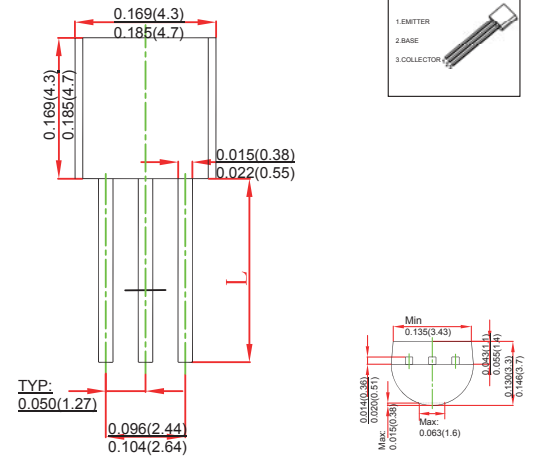
FEATURES

- General Purpose Switching and Amplification.
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:TO-92 molded plastic
- Mounting position:any

TO-92



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	-80	V
V_{CE0}	Collector-Emitter Voltage	-80	V
V_{EB0}	Emitter-Base Voltage	-4	V
I_C	Collector Current -Continuous	-0.5	A
P_D	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	200	°C /W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.1mA, I_E = 0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.1mA, I_C = 0$	-4			V
Collector cut-off current	I_{CBO}	$V_{CB} = -80V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -60V, I_B = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -10mA$	100			
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -100mA$	100			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$			-0.25	V
Base-emitter voltage	V_{BE}	$I_C = -100mA, V_{CE} = -1V$			-1.2	V
Transition frequency	f_T	$V_{CE} = -1V, I_C = -100mA, f = 100MHz$	50			MHz

Marking	MPSA56
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RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

